

COMPLEMENTARY HIGH-POWER SILICON POWER TRANSISTORS

Applications

Linear and switching industrial Equipment

FEATURES

Complementary to TIP32C.

New enhanced series

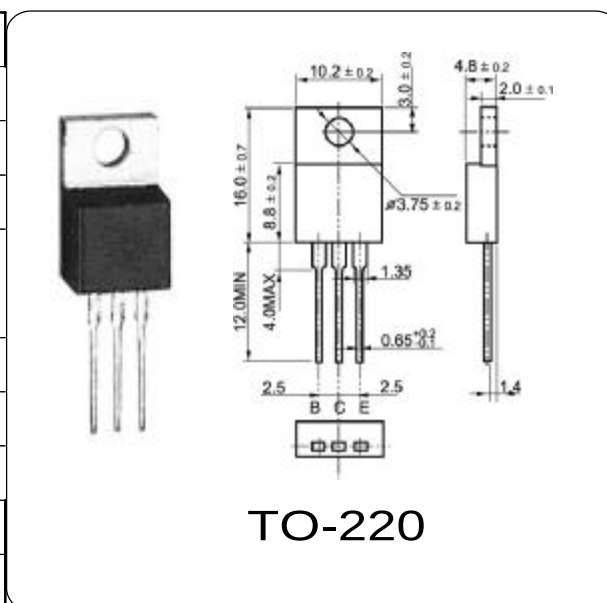
High switching speed

hFE improved linearity

Triple Diffused NPN Transistors

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	100	V
Collector-Emitter Voltage		V_{CEO}	100	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	3	A
	Pulse	I_{CP}	5	
Base Current		I_B	1	A
Collector Power Dissipation	Ta=25℃	P_C	2	W
	Tc=25℃		40	W
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55~150	℃



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Emitter Sustaining Voltage	$V_{CEO(SUS)}$	$I_C=30mA, I_B=0$	100	-	-	V
Collector Cut-off Current	I_{CEO}	$V_{CE}=60V, I_B=0$	-	-	0.3	mA
Collector Cut-off Current	I_{CES}	$V_{CE}=100V, V_{EB}=0$	-	-	200	μA
Emitter Cut-off Current	I_{EBO}	$V_{BE}=5V, I_C=0$	-	-	1	mA
DC Current Gain	h_{FE}	$V_{CE}=4V, I_C=1A$	25	-	-	
		$V_{CE}=4V, I_C=3A$	10	-	50	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=3A, I_B=375mA$	-	-	1.2	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=4V, I_C=3A$	-	-	1.8	V
Transition Frequency	f_T	$V_{CE}=10V, I_C=500mA$ $f=1MHz$	3.0	-	-	MHz

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